

Silicon PNP Power Transistors

2SA1250

DESCRIPTION

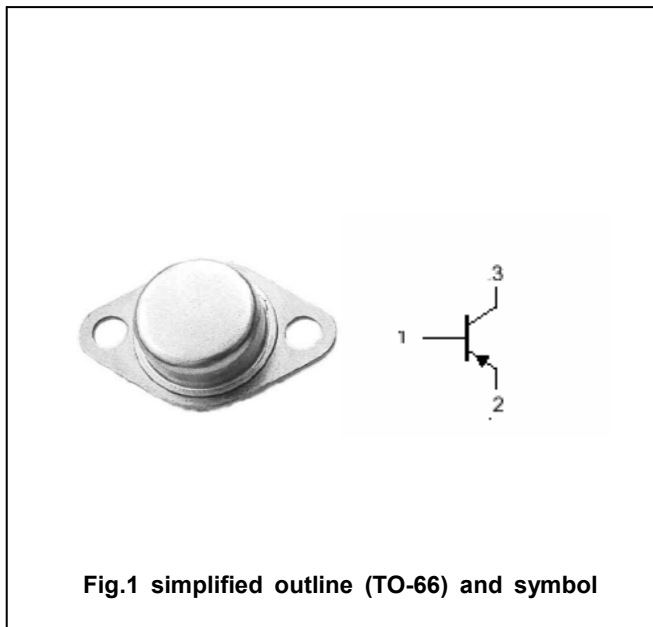
- With TO-66 package
- Excellent safe operating area
- High breakdown voltage

APPLICATIONS

- For general-purpose amplifier ;  
and switching applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	-200	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	-200	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-7	V
I <sub>C</sub>	Collector current		-8	A
P <sub>D</sub>	Total power dissipation	T <sub>C</sub> =25□	30	W
T <sub>j</sub>	Junction temperature		150	□
T <sub>stg</sub>	Storage temperature		-55~150	□

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## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-10mA ; I <sub>B</sub> =0	-200			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =-1mA ; I <sub>C</sub> =0	-7			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-5A; I <sub>B</sub> =-0.5A			-1.5	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =-5A; I <sub>B</sub> =-0.5A			-2.0	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =200V; I <sub>E</sub> =0			-10	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-7V; I <sub>C</sub> =0			-10	μA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =-2A ; V <sub>CE</sub> =-1V	40		200	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =-5A ; V <sub>CE</sub> =-1V	20			

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PACKAGE OUTLINE



Fig.2 outline dimensions